

### Low Noise Silicon Bipolar RF Transistor

- For broadband amplifiers up to 2 GHz and fast non-saturated switches at collector currents from 0.5 mA to 20 mA
- Pb-free (RoHS compliant) package
- Qualification report according to AEC-Q101 available





### **ESD** (Electrostatic discharge) sensitive device, observe handling precaution!

Туре	Marking	Pin Configuration			Package
BFR92P	GFs	1=B	2=E	3=C	SOT23

## **Maximum Ratings** at $T_A$ = 25 °C, unless otherwise specified

Parameter	Symbol	Value	Unit
Collector-emitter voltage	$V_{\sf CEO}$	15	V
Collector-emitter voltage	$V_{CES}$	20	
Collector-base voltage	$V_{\mathrm{CBO}}$	20	
Emitter-base voltage	$V_{EBO}$	2.5	
Collector current	I <sub>C</sub>	45	mA
Base current	/ <sub>B</sub>	4	
Total power dissipation <sup>1)</sup>	P <sub>tot</sub>	280	mW
<i>T</i> <sub>S</sub> ≤ 93 °C			
Junction temperature	$T_{J}$	150	°C
Storage temperature	$T_{Stq}$	-55 150	

#### **Thermal Resistance**

Parameter	Symbol	Value	Unit
Junction - soldering point <sup>2)</sup>	R <sub>thJS</sub>	205	K/W

 $<sup>{}^1</sup>T_{\rm S}$  is measured on the collector lead at the soldering point to the pcb

 $<sup>^2</sup>$ For the definition of  $R_{\text{thJS}}$  please refer to Application Note AN077 (Thermal Resistance Calculation)



# **Electrical Characteristics** at $T_A$ = 25 °C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	15	-	-	V
$I_{\rm C}$ = 1 mA, $I_{\rm B}$ = 0	, ,				
Collector-emitter cutoff current	I <sub>CES</sub>	-	_	10	μA
$V_{CE} = 20 \text{ V}, V_{BE} = 0$					
Collector-base cutoff current	I <sub>CBO</sub>	-	-	100	nA
$V_{\rm CB} = 10 \text{ V}, I_{\rm E} = 0$					
Emitter-base cutoff current	<i>I</i> <sub>EBO</sub>	-	-	100	μA
$V_{\rm EB} = 2.5  \rm V, I_{\rm C} = 0$					
DC current gain	h <sub>FE</sub>	70	100	140	-
$I_{\rm C}$ = 15 mA, $V_{\rm CE}$ = 8 V, pulse measured					



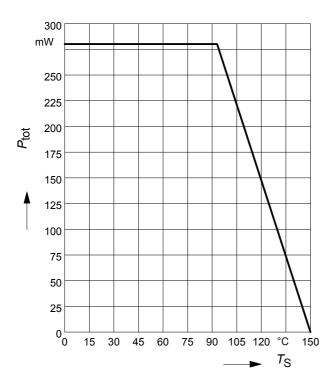
**Electrical Characteristics** at  $T_A$  = 25 °C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics (verified by random sampling	<u></u> ig)		1		
Transition frequency	f <sub>T</sub>	3.5	5	-	GHz
$I_{\rm C}$ = 15 mA, $V_{\rm CE}$ = 8 V, $f$ = 500 MHz					
Collector-base capacitance	C <sub>cb</sub>	-	0.39	0.55	pF
$V_{CB} = 10 \text{ V}, f = 1 \text{ MHz}, V_{BE} = 0$ ,					
emitter grounded					
Collector emitter capacitance	C <sub>ce</sub>	-	0.23	-	
$V_{CE} = 10 \text{ V}, f = 1 \text{ MHz}, V_{BE} = 0$ ,					
base grounded					
Emitter-base capacitance	C <sub>eb</sub>	-	0.64	-	
$V_{\text{EB}} = 0.5 \text{ V}, f = 1 \text{ MHz}, V_{\text{CB}} = 0$ ,					
collector grounded					
Minimum noise figure	NF <sub>min</sub>				dB
$I_{\rm C}$ = 2 mA, $V_{\rm CE}$ = 6 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$ ,					
f = 900 MHz		-	1.4	-	
$I_{\rm C}$ = 2 mA, $V_{\rm CE}$ = 6 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$ ,					
f = 1.8 GHz		-	2	-	
Power gain, maximum available <sup>1)</sup>	G <sub>ma</sub>				
$I_{\rm C}$ = 15 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$ , $Z_{\rm L}$ = $Z_{\rm Lopt}$ ,					
f = 900 MHz		-	16	-	
$I_{\rm C}$ = 15 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$ , $Z_{\rm L}$ = $Z_{\rm Lopt}$ ,					
f = 1.8 GHz		-	10.5	_	
Transducer gain	S <sub>21e</sub>   <sup>2</sup>				dB
$I_{\rm C}$ = 15 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm L}$ = 50 $\Omega$ ,					
f = 900 MHz		-	13	_	
$I_{\rm C}$ = 15 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm L}$ = 50 $\Omega$ ,					
f = 1.8 MHz		-	7.5	-	

 $<sup>^{1}</sup>G_{\text{ma}} = |S_{21e} / S_{12e}| (k-(k^{2}-1)^{1/2})$ 



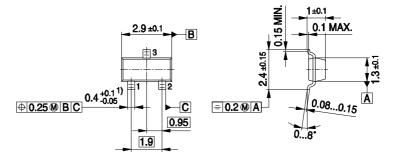
# Total power dissipation $P_{\text{tot}} = f(T_{\text{S}})$





## Package Outline

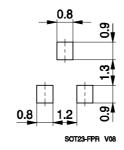




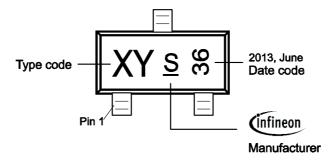
1) Lead width can be 0.6 max. in dambar area

SOT23-PO V08

### **Foot Print**

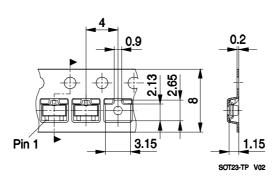


### **Marking Layout**



### **Standard Packing**

Reel o 180 mm: 3.000 Pieces / Reel Reel o 330 mm = 10.000 Pieces / Reel





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